

## MOSFET

Metal Oxide Semiconductor Field Effect Transistor

## OptiMOS™

OptiMOS™ 5 Power-Transistor, 80 V  
BSZ110N08NS5

## Data Sheet

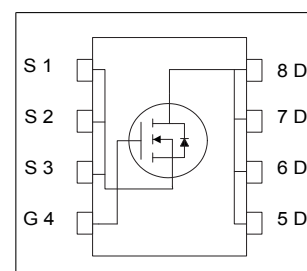
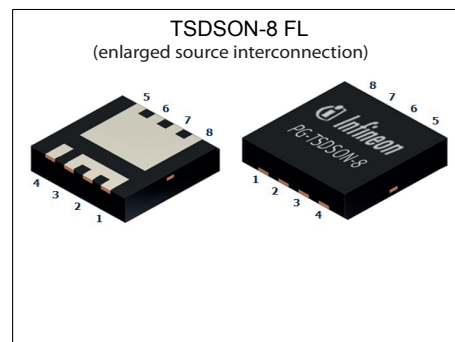
Rev. 2.1  
Final

Power Management & Multimarket

## 1 Description

### Features

- Ideal for high frequency switching and sync. rec.
- Optimized technology for DC/DC converters
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Very low on-resistance  $R_{DS(on)}$
- N-channel, normal level
- 100% avalanche tested
- Pb-free plating; RoHS compliant
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Halogen-free according to IEC61249-2-21
- Higher solder joint reliability with enlarged source interconnection



**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DS}$	80	V
$R_{DS(on),max}$	11.0	m $\Omega$
$I_D$	40	A
$Q_{oss}$	19	nC
$Q_G(0V..10V)$	15	nC

Type / Ordering Code	Package	Marking	Related Links
BSZ110N08NS5	PG-TSDSON-8 FL	110N08N	-

<sup>1)</sup> J-STD20 and JESD22

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## 2 Maximum ratings

at  $T_j = 25\text{ °C}$ , unless otherwise specified

**Table 2 Maximum ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	$I_D$	-	-	40 33	A	$T_C=25\text{ °C}$ $T_C=100\text{ °C}$
Pulsed drain current <sup>1)</sup>	$I_{D,pulse}$	-	-	160	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse <sup>2)</sup>	$E_{AS}$	-	-	40	mJ	$I_D=20\text{ A}$ , $R_{GS}=25\text{ }\Omega$
Gate source voltage	$V_{GS}$	-20	-	20	V	-
Power dissipation	$P_{tot}$	-	-	50	W	$T_C=25\text{ °C}$
Operating and storage temperature	$T_j, T_{stg}$	-55	-	150	°C	IEC climatic category; DIN IEC 68-1: 55/150/56

## 3 Thermal characteristics

**Table 3 Thermal characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$	-	1.5	2.5	K/W	-
Device on PCB, 6 cm <sup>2</sup> cooling area <sup>3)</sup>	$R_{thJA}$	-	-	60	K/W	-

<sup>1)</sup> See figure 3 for more detailed information

<sup>2)</sup> See figure 13 for more detailed information

<sup>3)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

## 4 Electrical characteristics

**Table 4 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	80	-	-	V	$V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2.2	3	3.8	V	$V_{DS}=V_{GS}$ , $I_D=22\text{ }\mu\text{A}$
Zero gate voltage drain current	$I_{DSS}$	-	0.1 10	1 100	$\mu\text{A}$	$V_{DS}=80\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ }^\circ\text{C}$ $V_{DS}=80\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=125\text{ }^\circ\text{C}$
Gate-source leakage current	$I_{GSS}$	-	1	100	nA	$V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	9.6 13.4	11.0 16.3	m $\Omega$	$V_{GS}=10\text{ V}$ , $I_D=20\text{ A}$ $V_{GS}=6\text{ V}$ , $I_D=5\text{ A}$
Gate resistance	$R_G$	-	1.4	2	$\Omega$	-
Transconductance	$g_{fs}$	17	33	-	S	$ V_{DS} >2 I_D R_{DS(on)max}$ , $I_D=20\text{ A}$

**Table 5 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	$C_{iss}$	-	1000	1300	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=40\text{ V}$ , $f=1\text{ MHz}$
Output capacitance <sup>1)</sup>	$C_{oss}$	-	180	235	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=40\text{ V}$ , $f=1\text{ MHz}$
Reverse transfer capacitance <sup>1)</sup>	$C_{rss}$	-	11	19	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=40\text{ V}$ , $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	9	-	ns	$V_{DD}=40\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=20\text{ A}$ , $R_{G,ext}=1.6\text{ }\Omega$
Rise time	$t_r$	-	3	-	ns	$V_{DD}=40\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=20\text{ A}$ , $R_{G,ext}=1.6\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	15	-	ns	$V_{DD}=40\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=20\text{ A}$ , $R_{G,ext}=1.6\text{ }\Omega$
Fall time	$t_f$	-	3	-	ns	$V_{DD}=40\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=20\text{ A}$ , $R_{G,ext}=1.6\text{ }\Omega$

**Table 6 Gate charge characteristics<sup>2)</sup>**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	$Q_{gs}$	-	4.9	-	nC	$V_{DD}=40\text{ V}$ , $I_D=20\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge <sup>1)</sup>	$Q_{gd}$	-	3.3	5	nC	$V_{DD}=40\text{ V}$ , $I_D=20\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	$Q_{sw}$	-	5.4	-	nC	$V_{DD}=40\text{ V}$ , $I_D=20\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total	$Q_g$	-	15	18.5	nC	$V_{DD}=40\text{ V}$ , $I_D=20\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	4.9	-	V	$V_{DD}=40\text{ V}$ , $I_D=20\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total, sync. FET	$Q_{g(sync)}$	-	13	-	nC	$V_{DS}=0.1\text{ V}$ , $V_{GS}=0\text{ to }10\text{ V}$
Output charge <sup>1)</sup>	$Q_{oss}$	-	19	26	nC	$V_{DD}=40\text{ V}$ , $V_{GS}=0\text{ V}$

<sup>1)</sup> Defined by design. Not subject to production test

<sup>2)</sup> See "Gate charge waveforms" for parameter definition

**Table 7 Reverse diode**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	$I_S$	-	-	40	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	160	A	$T_C=25\text{ °C}$
Diode forward voltage	$V_{SD}$	-	0.88	1.2	V	$V_{GS}=0\text{ V}, I_F=20\text{ A}, T_J=25\text{ °C}$
Reverse recovery time <sup>1)</sup>	$t_{rr}$	-	36	72	ns	$V_R=40\text{ V}, I_F=20\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge <sup>1)</sup>	$Q_{rr}$	-	36	72	nC	$V_R=40\text{ V}, I_F=20\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$

<sup>1)</sup> Defined by design. Not subject to production test

## 5 Electrical characteristics diagrams

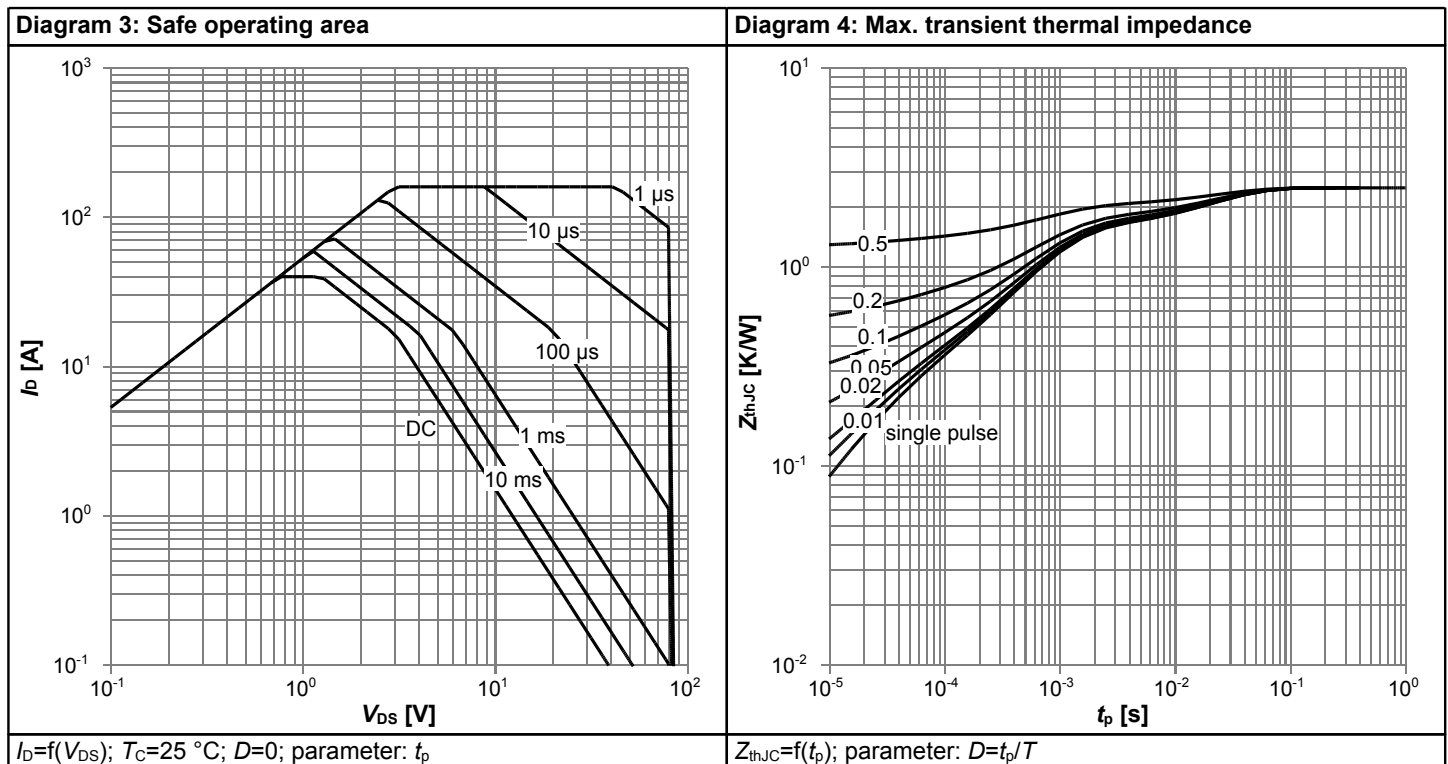
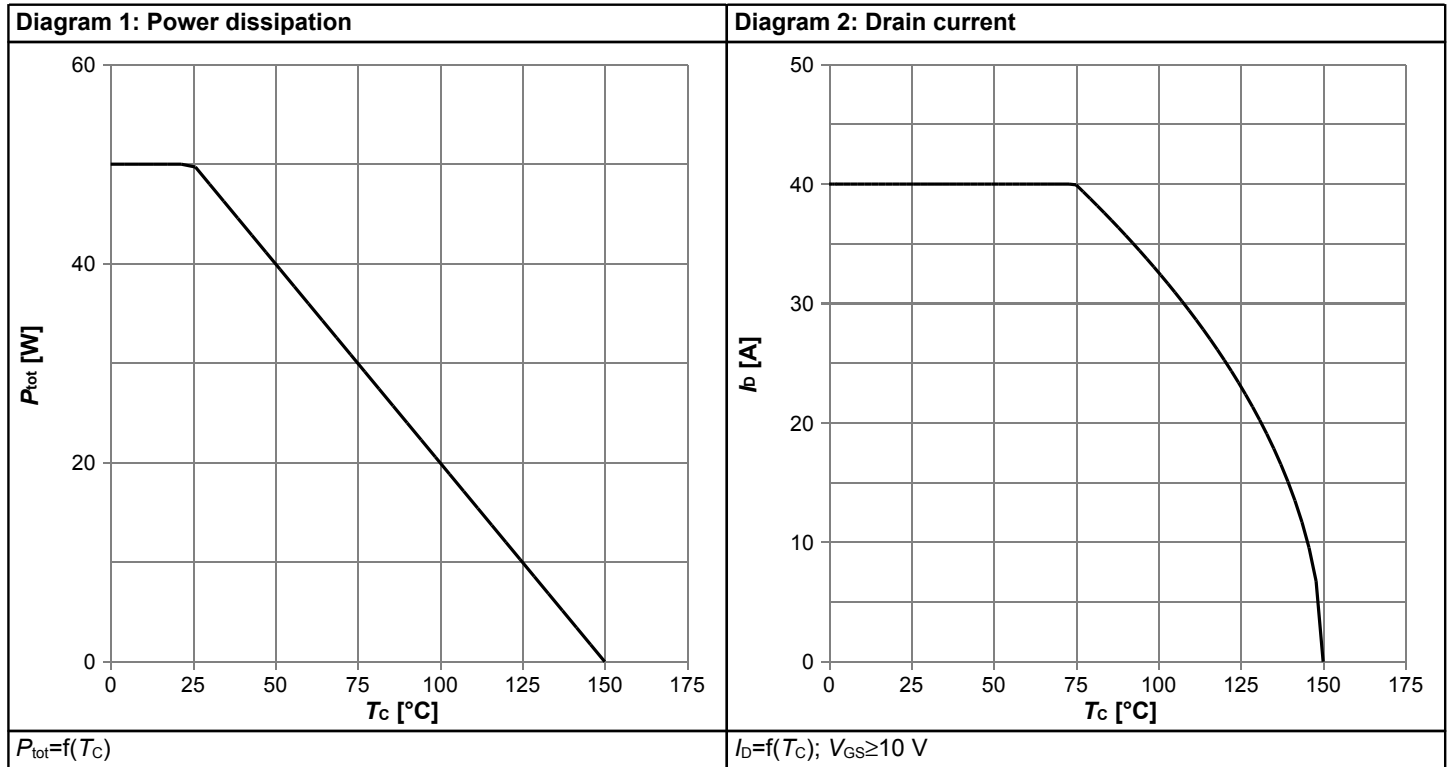
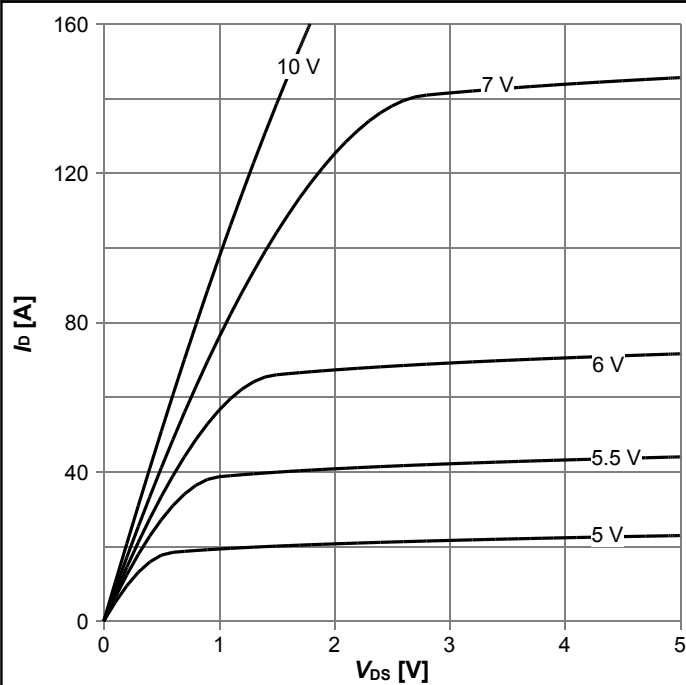
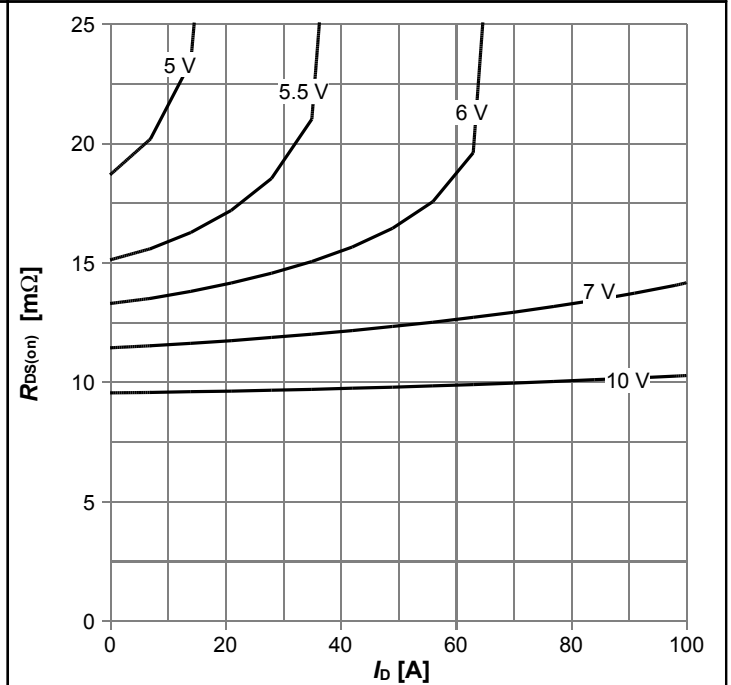


Diagram 5: Typ. output characteristics



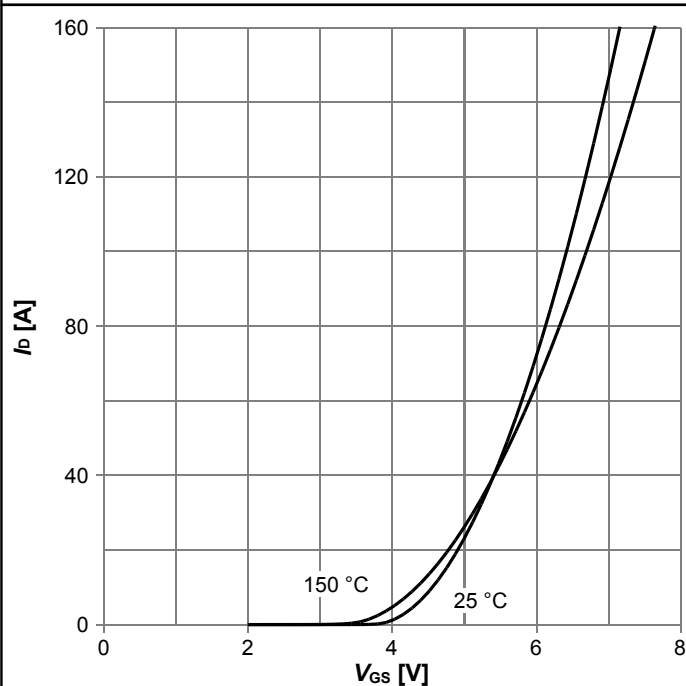
$I_D=f(V_{DS}); T_j=25\text{ }^\circ\text{C};$  parameter:  $V_{GS}$

Diagram 6: Typ. drain-source on resistance



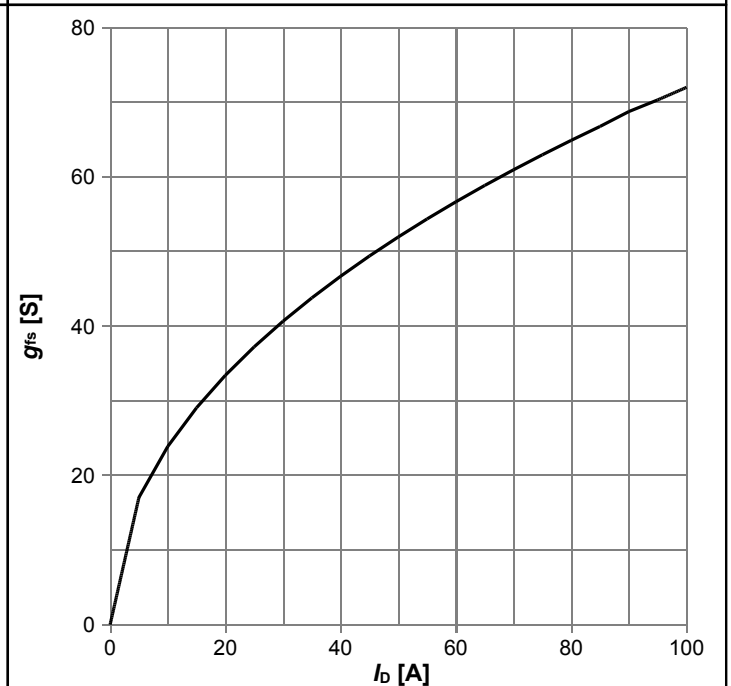
$R_{DS(on)}=f(I_D); T_j=25\text{ }^\circ\text{C};$  parameter:  $V_{GS}$

Diagram 7: Typ. transfer characteristics



$I_D=f(V_{GS}); |V_{DS}|>2|I_D|R_{DS(on)max};$  parameter:  $T_j$

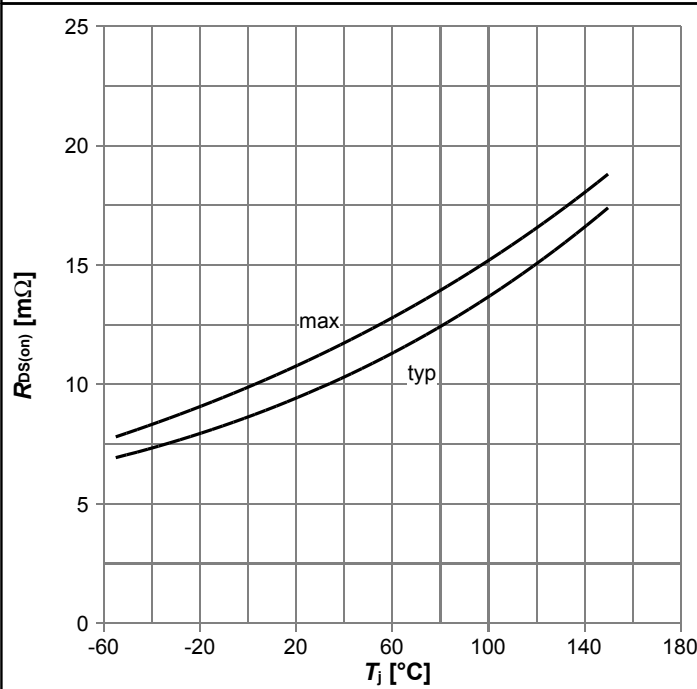
Diagram 8: Typ. forward transconductance



$g_{fs}=f(I_D); T_j=25\text{ }^\circ\text{C}$

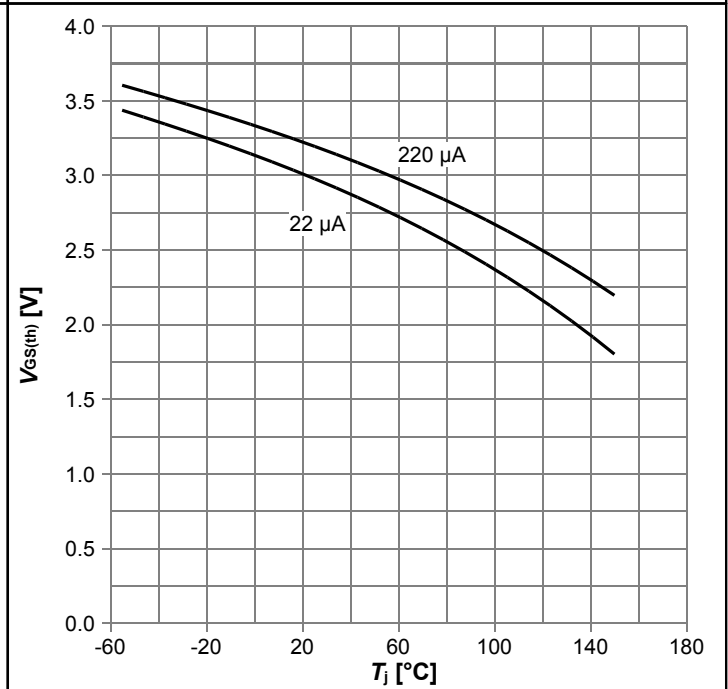


Diagram 9: Drain-source on-state resistance



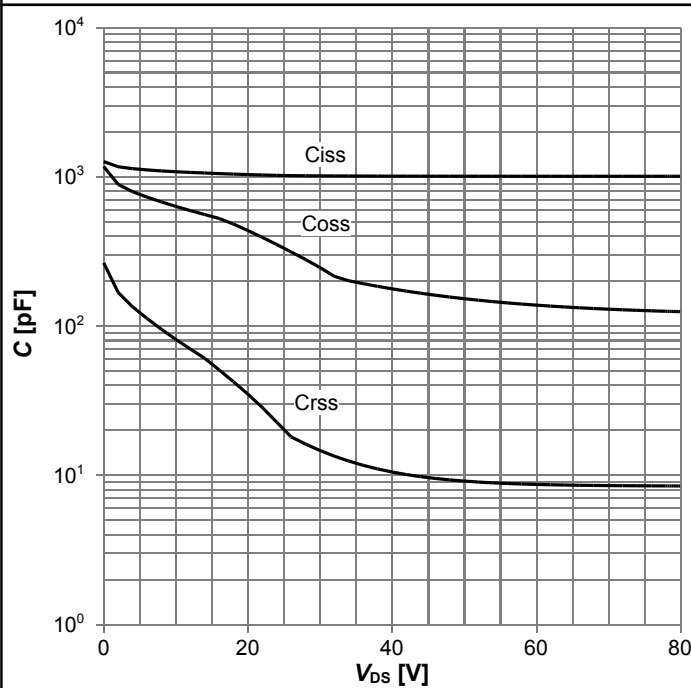
$R_{DS(on)}=f(T_j); I_D=20\text{ A}; V_{GS}=10\text{ V}$

Diagram 10: Typ. gate threshold voltage



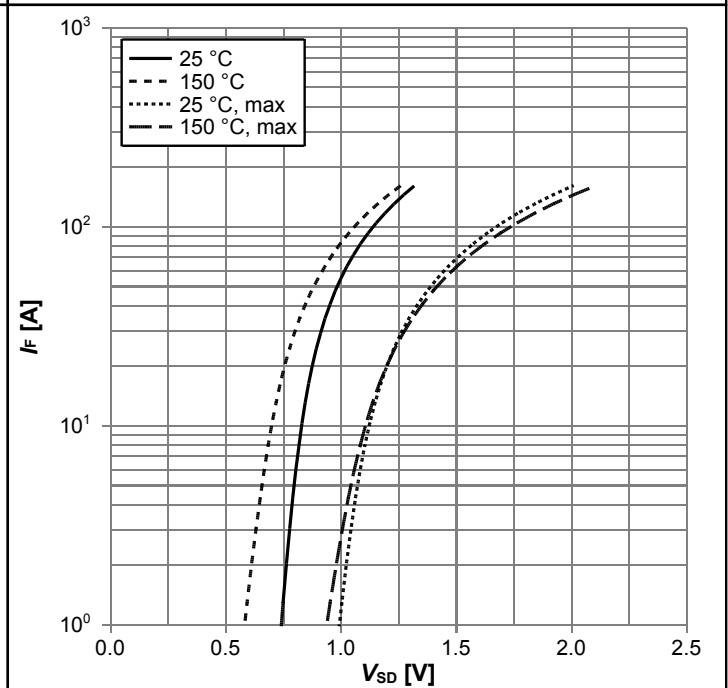
$V_{GS(th)}=f(T_j); V_{GS}=V_{DS}; \text{parameter: } I_D$

Diagram 11: Typ. capacitances



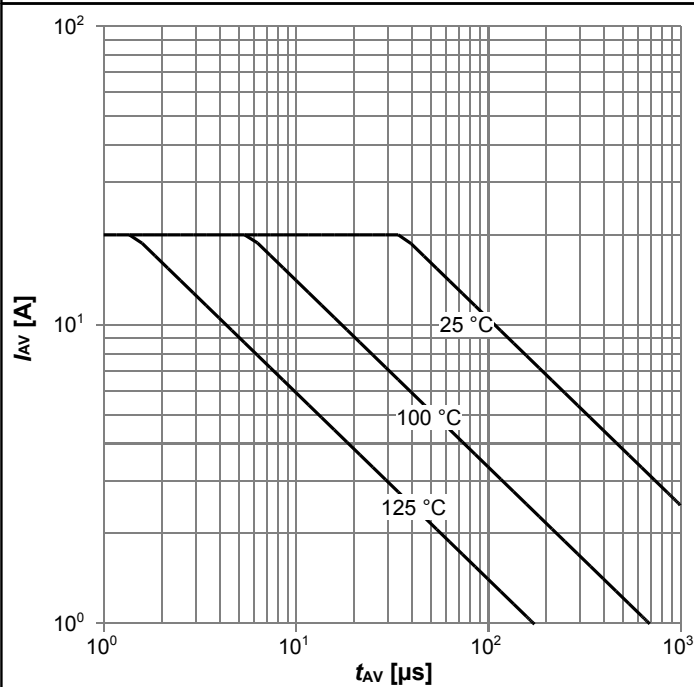
$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$

Diagram 12: Forward characteristics of reverse diode



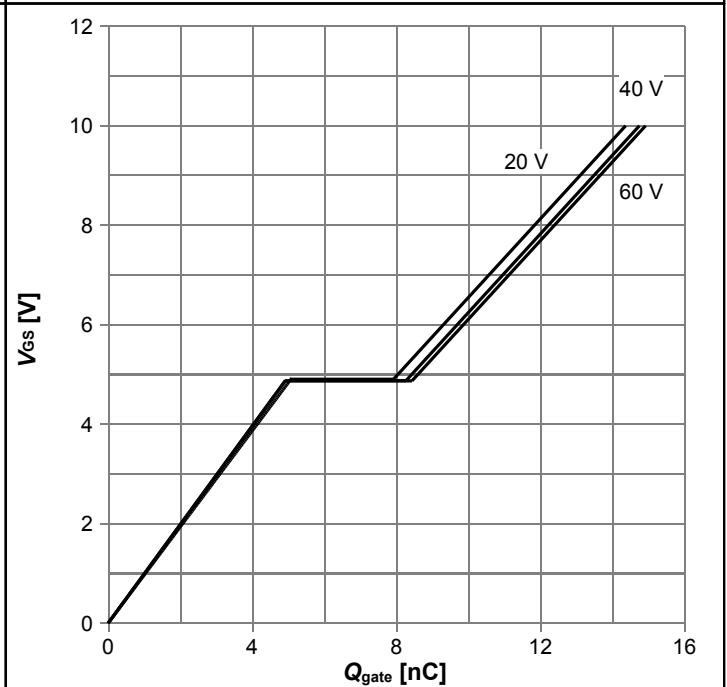
$I_F=f(V_{SD}); \text{parameter: } T_j$

Diagram 13: Avalanche characteristics



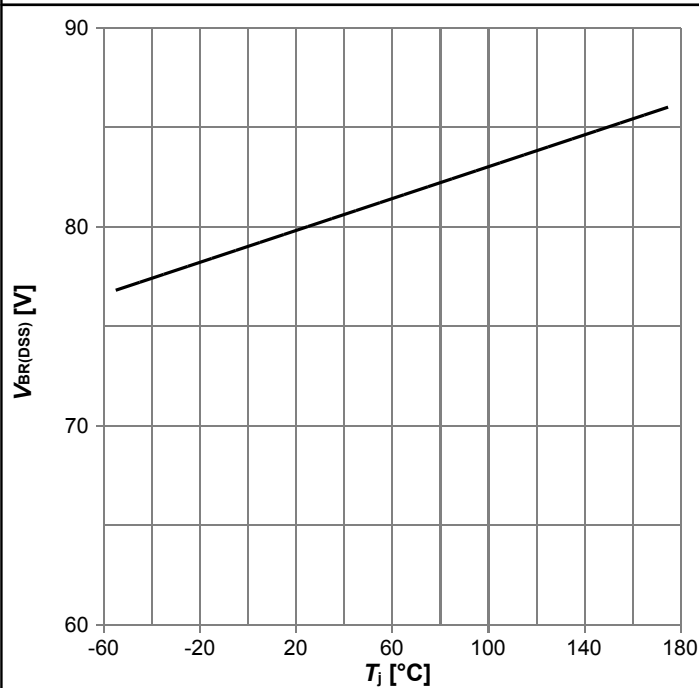
$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$ ; parameter:  $T_{j(start)}$

Diagram 14: Typ. gate charge



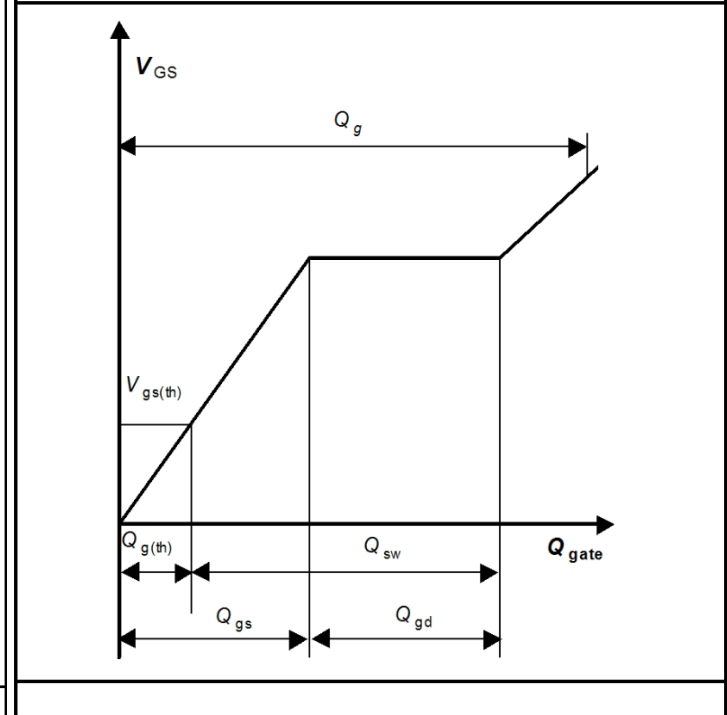
$V_{GS}=f(Q_{gate}); I_D=20$  A pulsed; parameter:  $V_{DD}$

Diagram 15: Drain-source breakdown voltage



$V_{BR(DSS)}=f(T_j); I_D=1$  mA

Gate charge waveforms



6 Package Outlines

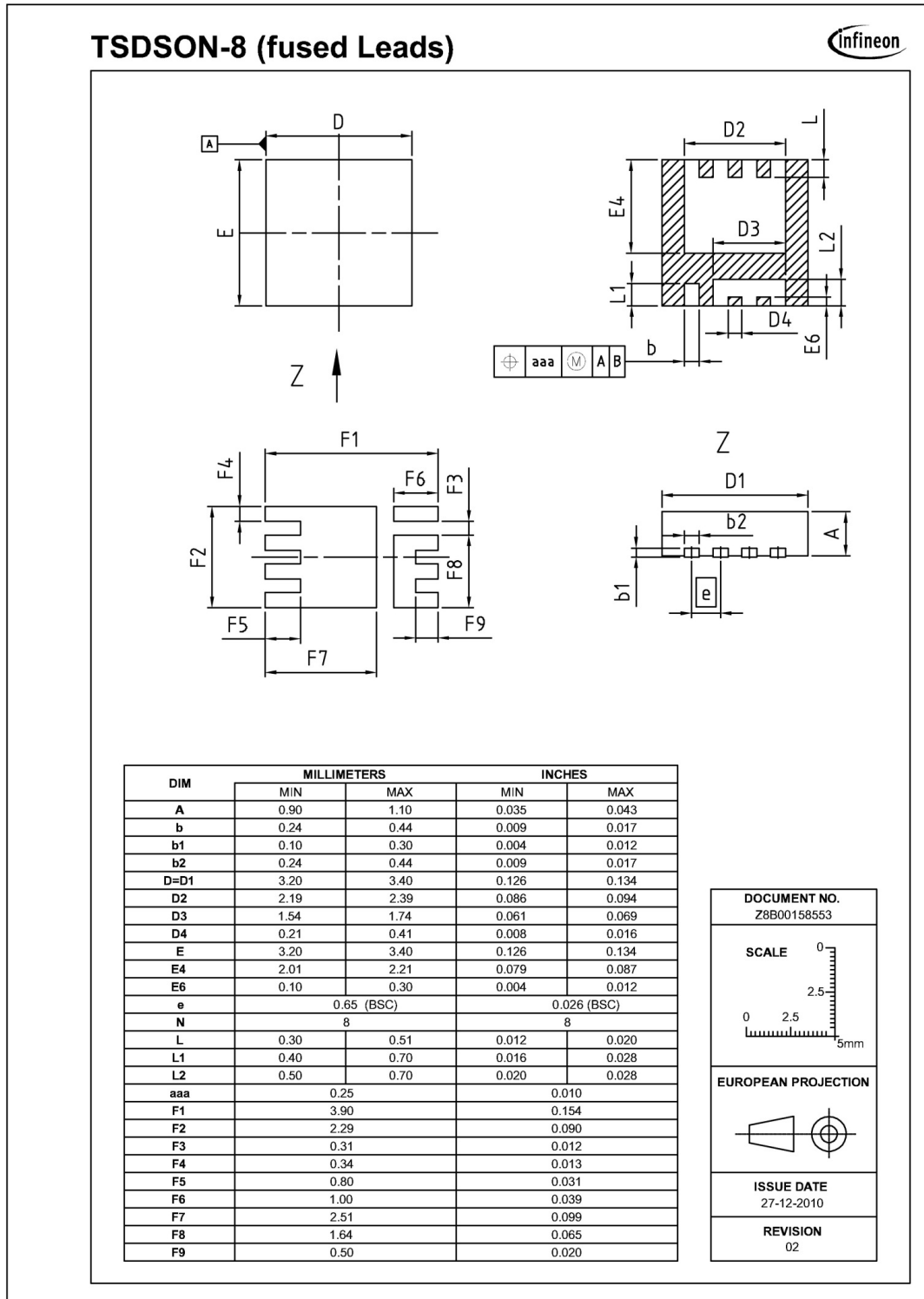


Figure 1 Outline PG-TSDSON-8 FL, dimensions in mm/inches

## Revision History

BSZ110N08NS5

**Revision: 2014-05-05, Rev. 2.1**

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.1	2014-05-05	Release of Final Version

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